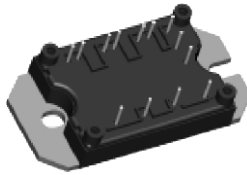


## Three Phase Inverter Module in MTP Package 1200 V NPT IGBT and HEXFRED® Diodes, 15 A


**MTP**

PRODUCT SUMMARY	
$V_{CES}$	1200 V
$V_{CE(on)}$ typical at $V_{GE} = 15$ V	2.51 V
$I_C$ at $T_C = 100$ °C	15 A
$t_{sc}$ at $T_J = 150$ °C	> 10 $\mu$ s

**FEATURES**

- Generation 5 NPT 1200 V IGBT technology
- HEXFRED® diode with ultrasoft reverse recovery
- Very low conduction and switching losses
- Optional SMT thermistor (NTC)
- Aluminum oxide DBC
- Very low stray inductance design for high speed operation
- Short circuit 10  $\mu$ s
- Square RBSOA
- Operating frequencies 8 kHz to 60 kHz
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level


**RoHS**  
COMPLIANT

**BENEFITS**

- Optimized for inverter motor drive applications
- Low EMI, requires less snubbing
- Direct mounting to heatsink
- PCB solderable terminals
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		1200	V
Continuous collector current	$I_C$	$T_C = 25$ °C	30	A
		$T_C = 100$ °C	15	
Pulsed collector current	$I_{CM}$		60	
Peak switching current	$I_{LM}$		60	
Diode continuous forward current	$I_F$	$T_C = 100$ °C	15	
Peak diode forward current	$I_{FM}$		30	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
RMS isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1$ min	2500	
Maximum power dissipation (including diode and IGBT)	$P_D$	$T_C = 25$ °C	187	W
		$T_C = 100$ °C	75	

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	1200	-	-	V
Temperature coefficient of $V_{(BR)CES}$	$\Delta V_{(BR)CES}/\Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	-	1.11	-	V/ $^\circ\text{C}$
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 15\text{ A}$	-	2.51	2.70	V
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$	-	3.36	3.66	
		$V_{GE} = 15\text{ V}, I_C = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.94	3.16	
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	4.12	4.46	
Gate threshold voltage	$V_{GE(th)}$	$I_C = 250\text{ }\mu\text{A}$	4	-	6	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	-	- 10	-	mV/ $^\circ\text{C}$
Forward transconductance	$g_{fe}$	$V_{CE} = 25\text{ V}, I_C = 15\text{ A}$	-	12	-	S
Collector to emitter leaking current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	-	-	250	$\mu\text{A}$
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	1000	
Diode forward voltage drop	$V_{FM}$	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	-	2.13	2.58	V
		$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	-	2.70	3.33	
		$I_F = 15\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	2.27	2.75	
		$I_F = 30\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	3.06	3.76	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 250$	nA

<b>SWITCHING CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	$Q_g$	$I_C = 15\text{ A}$ $V_{CC} = 600\text{ V}$ $V_{GE} = 15\text{ V}$	-	98	146	nC
Gate to emitter charge (turn-on)	$Q_{ge}$		-	12	17	
Gate to collector charge (turn-on)	$Q_{gc}$		-	46	69	
Turn-on switching loss	$E_{on}$	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $R_g = 10\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$ Energy losses include tail and diode reverse recovery	-	0.990	1.485	mJ
Turn-off switching loss	$E_{off}$		-	0.827	1.241	
Total switching loss	$E_{ts}$		-	1.817	2.726	
Turn-on switching loss	$E_{on}$	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $R_g = 10\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$ Energy losses include tail and diode reverse recovery	-	1.352	2.028	mJ
Turn-off switching loss	$E_{off}$		-	1.138	1.707	
Total switching loss	$E_{ts}$		-	2.490	3.735	
Turn-on delay time	$t_{d(on)}$	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $L = 500\text{ }\mu\text{H}, L_S = 100\text{ nH}$ $R_g = 10\text{ }\Omega, T_J = 125\text{ }^\circ\text{C}$	-	95	143	ns
Rise time	$t_r$		-	18	27	
Turn-off delay time	$t_{d(off)}$		-	134	200	
Fall time	$t_f$		-	227	341	
Reverse BIAS safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 60\text{ A}$ $R_g = 10\text{ }\Omega, V_{GE} = 15\text{ V to }0$	Fullsquare			
Short circuit safe operating area	SCSOA	$V_{CC} = 600\text{ V}, V_{GE} = +15\text{ V to }0$ $T_J = 150\text{ }^\circ\text{C}, V_P = 1200\text{ V}, R_g = 10\text{ }\Omega$	10	-	-	$\mu\text{s}$
Input capacitance	$C_{ies}$	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1\text{ MHz}$	-	1302	1953	pF
Output capacitance	$C_{oes}$		-	717	1076	
Reverse transfer capacitance	$C_{res}$		-	38	57	
Diode reverse recovery energy	$E_{rec}$	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $L = 500\text{ }\mu\text{H}, L_S = 100\text{ nH}$ $R_g = 10\text{ }\Omega, T_J = 125\text{ }^\circ\text{C}$	-	819	-	$\mu\text{J}$
Diode reverse recovery time	$t_{rr}$		-	96	-	ns
Diode peak reverse current	$I_{rr}$		-	35	-	A



THERMISTOR SPECIFICATIONS (T CODE ONLY)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Resistance	$R_0$ <sup>(1)</sup>	$T_0 = 25\text{ }^\circ\text{C}$	-	30	-	k $\Omega$
Sensitivity index of the thermistor material	$\beta$ <sup>(1)(2)</sup>	$T_0 = 25\text{ }^\circ\text{C}$ $T_1 = 85\text{ }^\circ\text{C}$	-	4000	-	K

**Notes**

<sup>(1)</sup>  $T_0, T_1$  are thermistor's temperatures

<sup>(2)</sup>  $\frac{R_0}{R_1} = \exp\left[\beta\left(\frac{1}{T_0} - \frac{1}{T_1}\right)\right]$

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	$T_J$		- 40	-	150	$^\circ\text{C}$
Storage temperature range	$T_{Stg}$		- 40	-	125	
Junction to case	IGBT	$R_{thJC}$	-	-	1.1	$^\circ\text{C/W}$
	Diode		-	-	1.7	
	Module		-	0.50	-	
Case to sink per module	$R_{thCS}$	Heatsink compound thermal conductivity = 1 W/mK	-	0.1	-	
Mounting torque			-	-	4	Nm
Weight			-	65	-	g

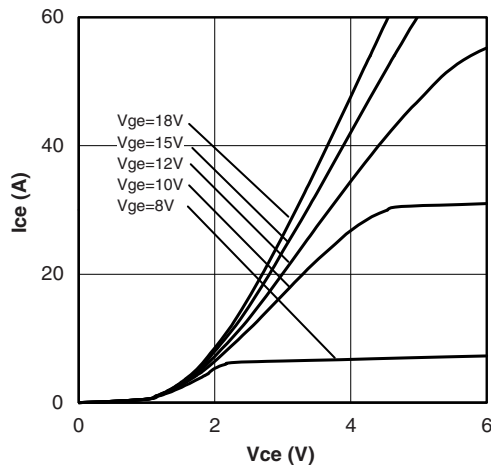


Fig. 1 - Typical Output Characteristics  
 $T_J = 25\text{ }^\circ\text{C}$

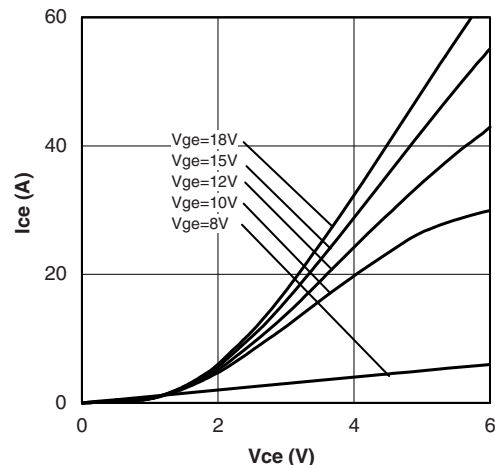


Fig. 2 - Typical Output Characteristics  
 $T_J = 125\text{ }^\circ\text{C}$

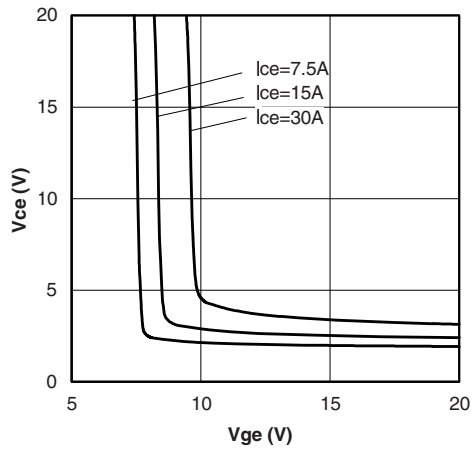


Fig. 3 - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 25\text{ }^\circ\text{C}$

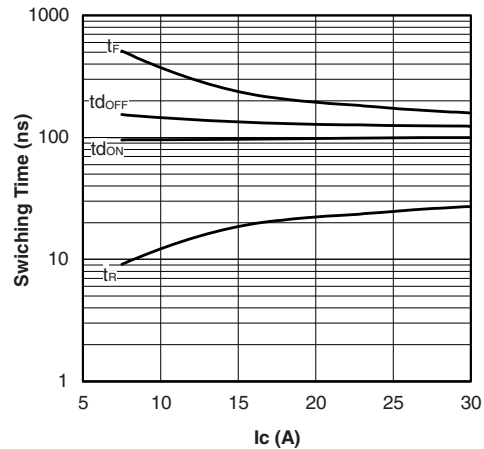


Fig. 6 - Typical Switching Time vs.  $I_C$   
 $T_J = 125\text{ }^\circ\text{C}$ ,  $L = 500\text{ }\mu\text{H}$ ,  $V_{CE} = 600\text{ V}$   
 $R_g = 10\text{ }\Omega$ ;  $V_{GE} = 15\text{ V}$

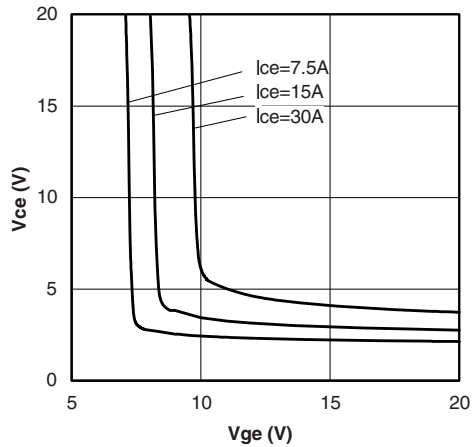


Fig. 4 - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 125\text{ }^\circ\text{C}$

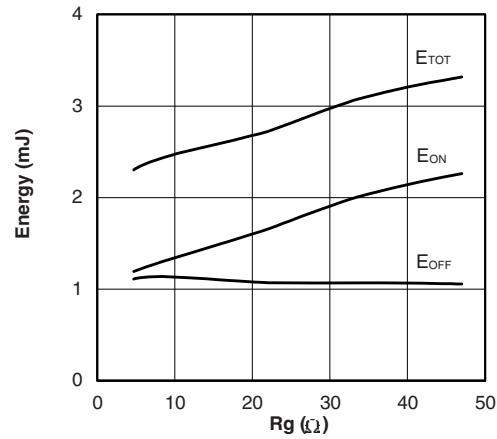


Fig. 7 - Typical Energy Loss vs.  $R_g$   
 $T_J = 125\text{ }^\circ\text{C}$ ,  $L = 500\text{ }\mu\text{H}$ ,  $V_{CE} = 600\text{ V}$   
 $I_C = 15\text{ A}$ ;  $V_{GE} = 15\text{ V}$

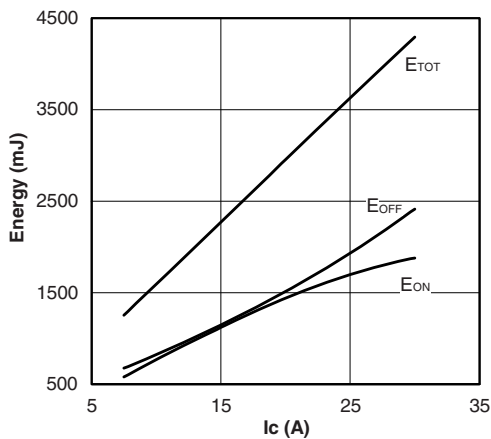


Fig. 5 - Typical Energy Loss vs.  $I_C$   
 $T_J = 125\text{ }^\circ\text{C}$ ,  $L = 500\text{ }\mu\text{H}$ ,  $V_{CE} = 600\text{ V}$   
 $R_g = 10\text{ }\Omega$ ;  $V_{GE} = 15\text{ V}$

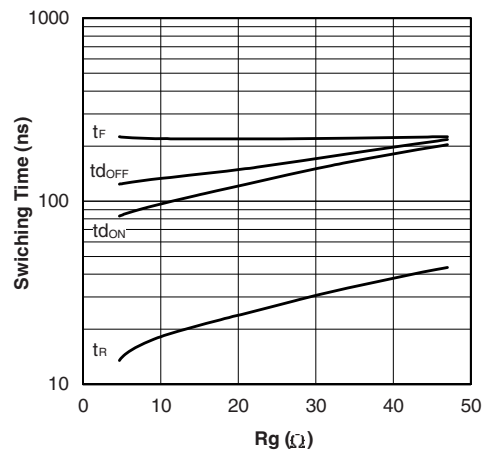


Fig. 8 - Typical Switching Time vs.  $R_g$   
 $T_J = 125\text{ }^\circ\text{C}$ ,  $L = 500\text{ }\mu\text{H}$ ,  $V_{CE} = 600\text{ V}$   
 $I_C = 15\text{ A}$ ;  $V_{GE} = 15\text{ V}$

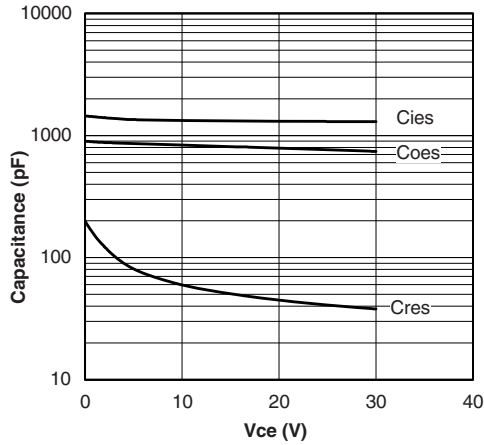


Fig. 9 - Typical Capacitance vs.  $V_{CE}$   
 $V_{GE} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

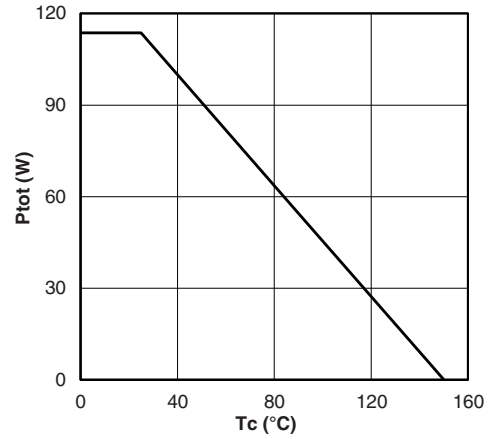


Fig. 12 - Power Dissipation vs. Case Temperature  
(IGBT only)

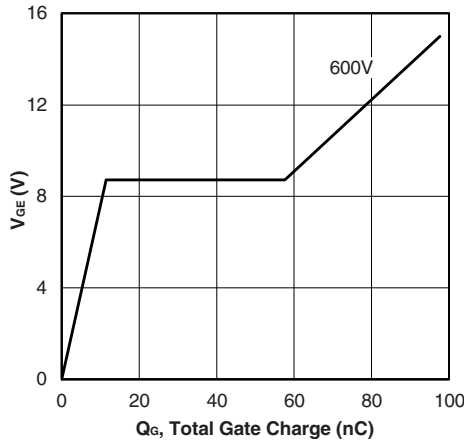


Fig. 10 - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE} = 15 \text{ A}$

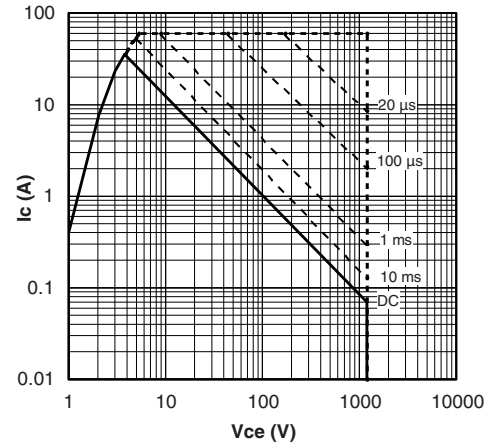


Fig. 13 - Forward SOA  
 $T_C = 25 \text{ }^\circ\text{C}$ ,  $T_J \leq 150 \text{ }^\circ\text{C}$

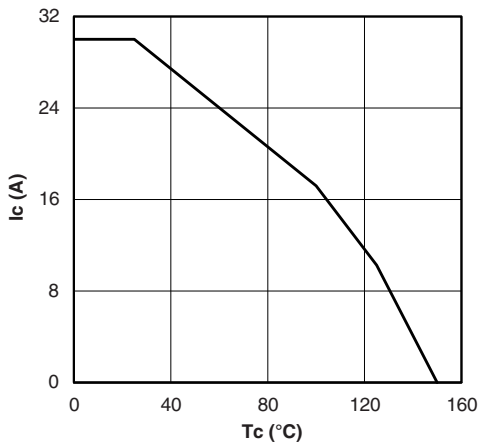


Fig. 11 - Maximum DC Collector Current vs. Case Temperature

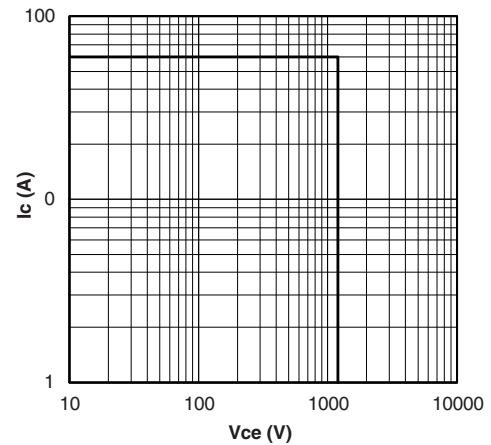


Fig. 14 - Reverse BIAS SOA  
 $T_J = 150 \text{ }^\circ\text{C}$ ,  $V_{GE} = 15 \text{ V}$

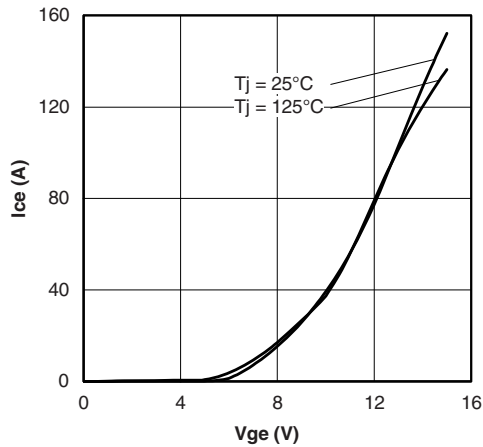


Fig. 15 - Typical Transfer Characteristics  
 $V_{CE} = 50 \text{ V}$ ;  $t_p = 10 \mu\text{s}$

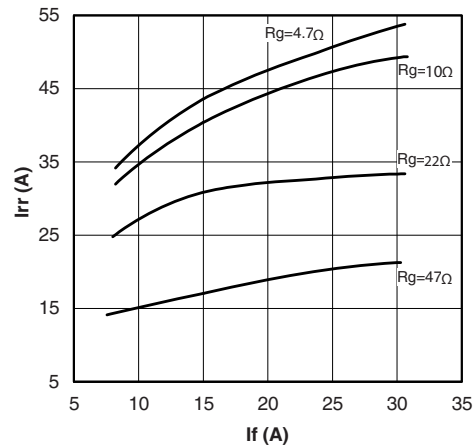


Fig. 17 - Typical Diode  $I_{rr}$  vs.  $I_F$   
 $T_J = 125^\circ\text{C}$

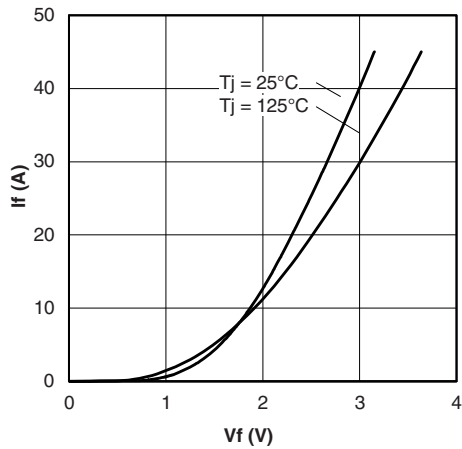


Fig. 16 - Typical Diode Forward Characteristics  
 $t_p = 80 \mu\text{s}$

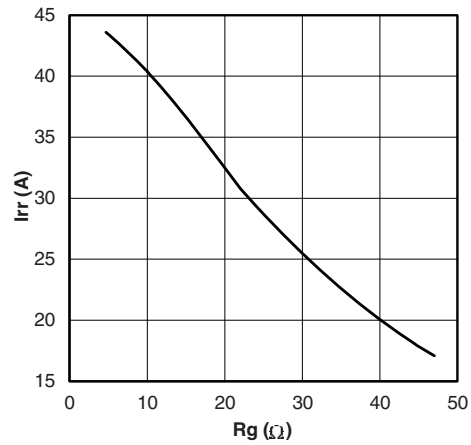


Fig. 18 - Typical Diode  $I_{rr}$  vs.  $R_g$   
 $T_J = 125^\circ\text{C}$ ;  $I_F = 10 \text{ A}$

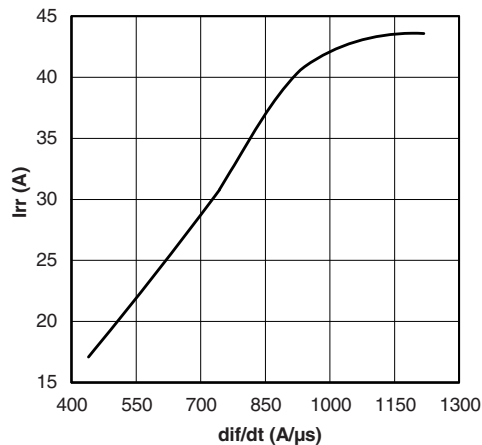


Fig. 19 - Typical Diode  $I_{rr}$  vs.  $di/dt$ ;  $V_{CC} = 600 \text{ V}$ ;  
 $V_{GE} = 15 \text{ V}$ ;  $I_{CE} = 10 \text{ A}$ ,  $T_J = 125^\circ\text{C}$



Three Phase Inverter Module in MTP Package Vishay Semiconductors  
 1200 V NPT IGBT and HEXFRED® Diodes, 15 A

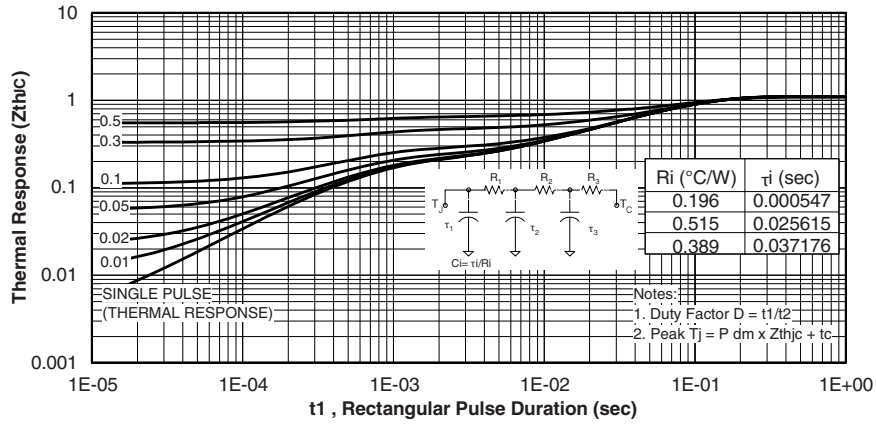


Fig. 20 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

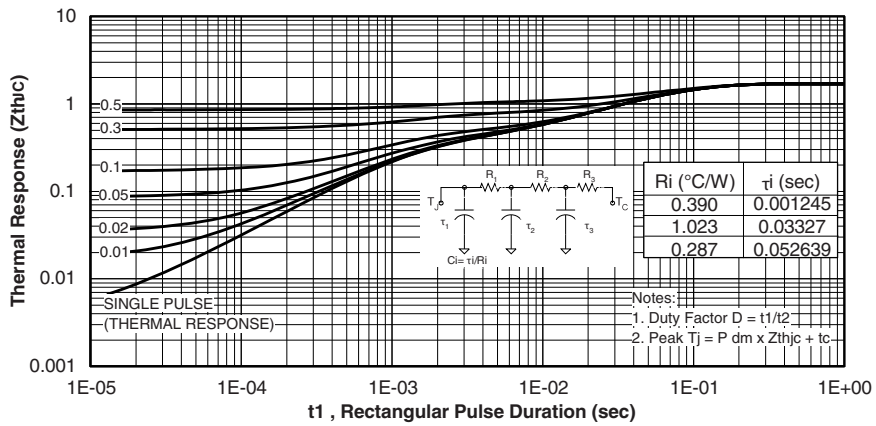


Fig. 21 - Maximum Transient Thermal Impedance, Junction to Case (Diode)

# GB15XP120KTPbF



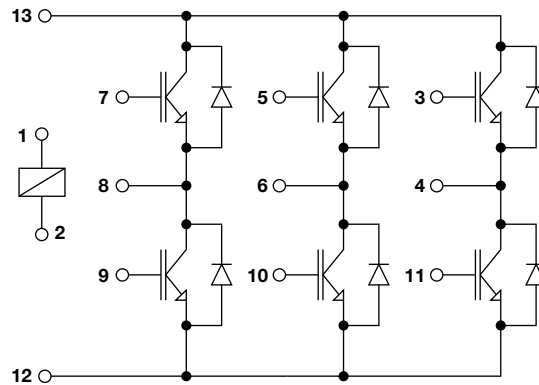
Vishay Semiconductors Three Phase Inverter Module in MTP Package  
1200 V NPT IGBT and HEXFRED® Diodes, 15 A

## ORDERING INFORMATION TABLE

Device code	<b>GB</b>	<b>15</b>	<b>XP</b>	<b>120</b>	<b>K</b>	<b>T</b>	<b>PbF</b>
	①	②	③	④	⑤	⑥	⑦

- 1** - IGBT module
- 2** - Nominal current rating (15 = 15 A)
- 3** - Circuit configuration (XP = Three phase inverter)
- 4** - Voltage code (120 = 1200 V)
- 5** - Speed/type (K = Ultrafast IGBT/inverter motor drive application)
- 6** - Special option:
  - None = No special option
  - T = Thermistor
- 7** - PbF = Lead (Pb)-free

## CIRCUIT CONFIGURATION



### LINKS TO RELATED DOCUMENTS

Dimensions	<a href="http://www.vishay.com/doc?95175">www.vishay.com/doc?95175</a>
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